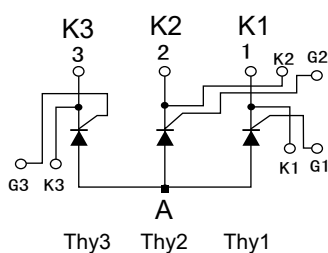
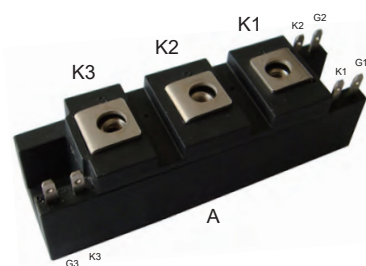
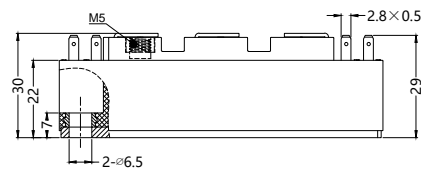


3TA80GKXXNB-B

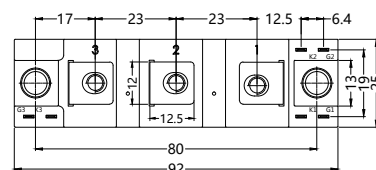
Three Phase Thyristor Module (Half Bridge)



Dimensions in mm (1mm = 0.0394")



Type	V_{RSM} V	V_{RRM} V
3TA80GK03NB-B	400	300
3TA80GK04NB-B	500	400
3TA80GK06NB-B	700	600



Symbol	Test Conditions	Maximum Ratings	Unit
$I_{T(AV)}$ $I_{T(RMS)}$	Single phase, half wave, 180°C conduction, $T_c=114^\circ\text{C}$	80 125	A
I_{TSM}	1/2cycle, 50Hz/60Hz, peak value, non-repetitive	2300/2500	A
I^2t		26000	A^2s
P_{GM} $P_{G(AV)}$		10 1	W
I_{FGM}		3	A
V_{FGM} V_{RGM}		10 5	V
di/dt	$I_G=150\text{mA}$, $T_j=25^\circ\text{C}$, $V_D=1/2V_{DRM}$, $dI_G/dt=1\text{A/us}$	60	A/us
T_{VJ} T_{VJM} T_{stg}		-30...+150 150 -30...+125	$^\circ\text{C}$
M_s M_t	to heatsink M6 to terminals M5	3 ~ 5 2.5 ~ 5	Nm
Weight		169	g

3TA80GKXXNB-B

Three Phase Thyristor Module (Half Bridge)

Symbol	Test Conditions	min.	typ.	max.	Unit
I_{DRM} I_{R RM}	at V _{DRM} , single phase, half wave, T _j =150°C			10 10	mA
V_{TM}	On-State Current 240A, T _j =25°C Inst. measurement			1.25	V
I_{GT}	T _j =25°C, I _T =1A, V _D =6V			150	mA
V_{GD}	T _j =150°C, V _D =1/2V _{DRM}	0.25			V
t_{gt}	I _T =100A, I _G =200mA, T _j =25°C, V _D =1/2V _{DRM} , di _G /dt=1A/us			10	us
dv/dt	T _j =150°C, V _D =2/3V _{DRM} , Exponential wave	150			V/us
I_H	T _j =25°C		100		mA
R_{thJC}	Junction to case (1/3 Module)			0.34	C/W

FEATURES

- * International standard package
- * Copper base plate
- * Glass passivated chips
- * RoHS compliant

APPLICATIONS

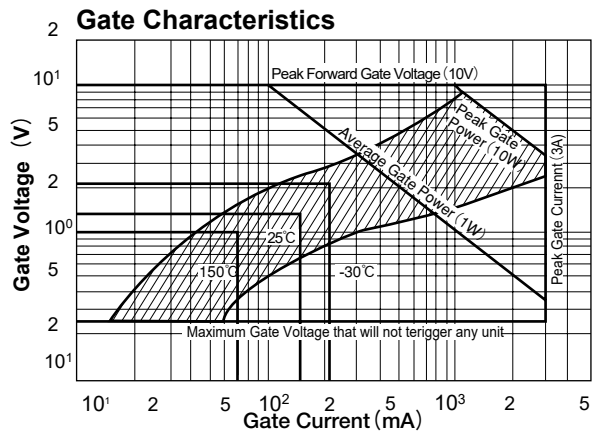
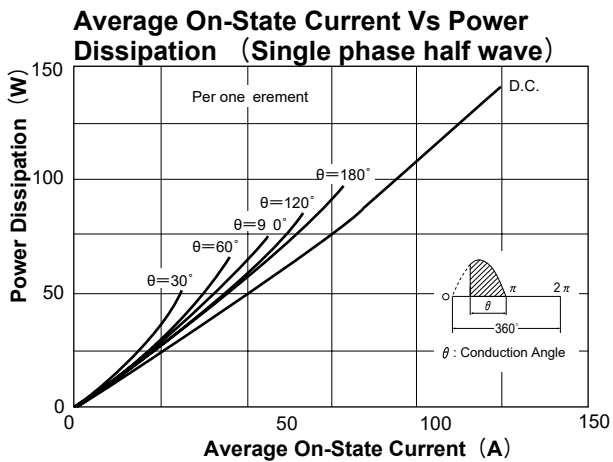
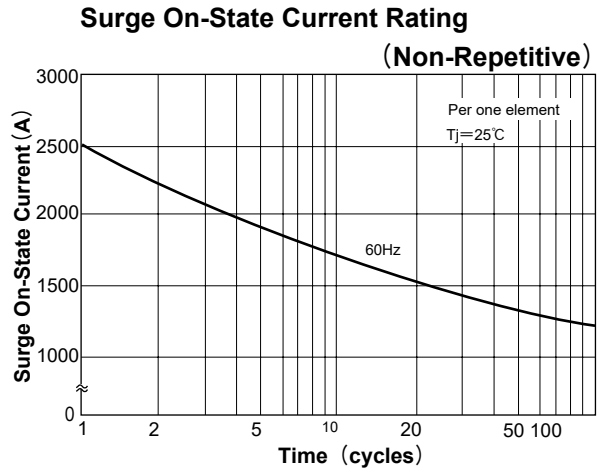
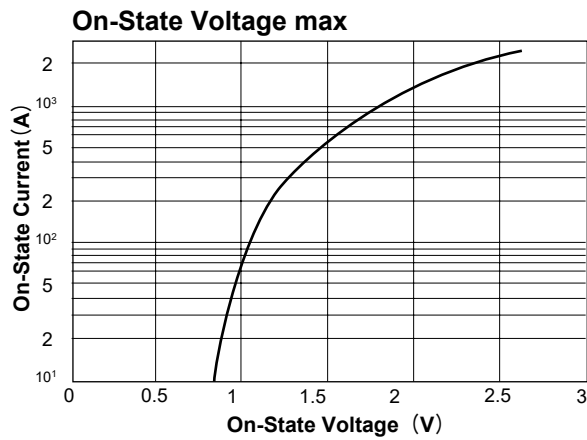
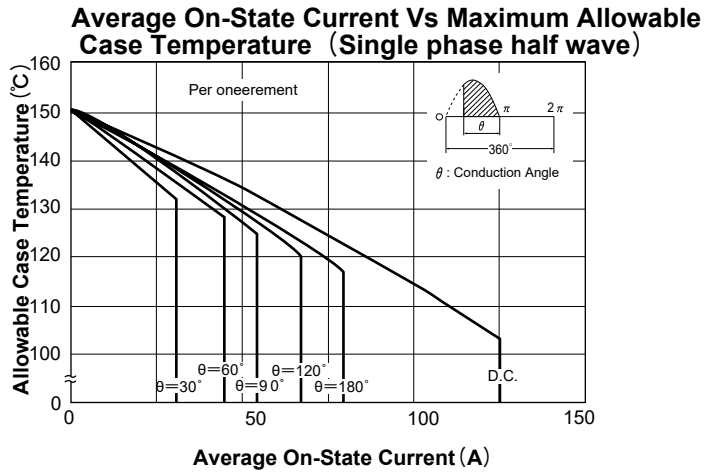
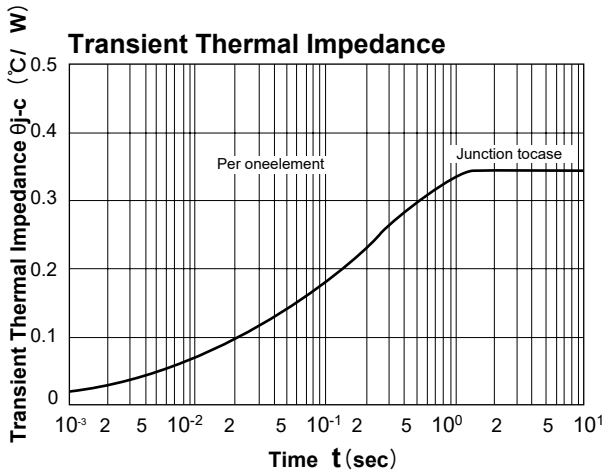
- * Welding Machine Power Supply
- * DC Power Supply

ADVANTAGES

- * Space and weight savings
- * Simple mounting with two screws
- * Improved temperature and power cycling
- * Reduced protection circuits

3TA80GKXXNB-B

Three Phase Thyristor Module (Half Bridge)



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